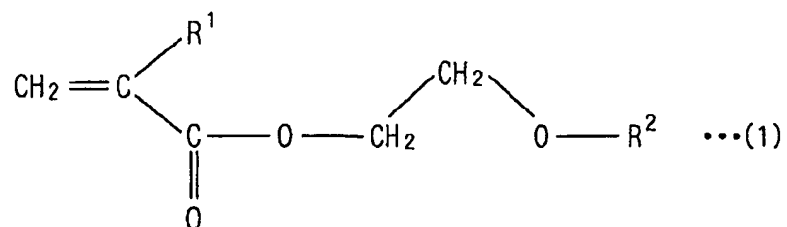


CLAIMS

1. A thick film photoresist composition comprising:
 - (A) a resin component containing (a) from 61 to 90% by weight of a structural
 - 5 unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group,
 - (B) a polymerizable compound containing at least one ethylenic unsaturated double bond,
 - (C) a photopolymerization initiator, and
 - 10 (D) an organic solvent.
2. A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).
- 15 3. A thick film photoresist composition according to claim 1, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



(wherein, R¹ represents a hydrogen atom or a methyl group, and R² represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

4. A thick film photoresist composition according to claim 1, wherein said
- 5 component (D) is at least one solvent selected from a group consisting of methyl isobutyl ketone and methyl ethyl ketone.
5. A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.
- 10 6. A pattern formed using said method disclosed in claim 5.